



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Shuji NAKAMURA et al.) Group:) Art Unit:
) Examiner:
Serial No.:))
Filed: January 25, 2000) POWER OF ATTORNEY BY ASSIGNEE
For: NITRIDE SEMICONDUCTOR DEVICE))
Assistant Commissioner for Patents Washington, D.C. 2023 1	-
Washington, D.C. 2023.	
Sir:	
Nichia Chemical Industries, Lt	d. Assignee of the above-identified
application by Assignment dated Dec. 24, 1999 h	ereby appoints the members of the firm of
HAVERSTOCK & OWENS LLP, a firm including Th	iomas B. Haverstock (Reg. No. 32,571) and Jonathan O.
Owens (Reg. No. 37,902) 260 Sheridan Avenue, Suite	420, Palo Alto, California 94306, telephone: (650) 833-
	full power of substitution to prosecute this application and
to transact all business in the Patent and Trademark O	
Please direct all correspondence regarding this	
Thomas B. Haverstock HAVERSTOCK & OWENS-LLP 260 Sheridan Avenue, Suite 420 Palo Alto, California 94306 Telephone: (650) 833-0160 Facsimile: (650) 833-0170	·
I hereby certify that the Assignment documen	t filed with the application or filed subsequent to the filing
date of the application, has been reviewed and I herebis with Nichia Chemical Industries, Ltd	y certify that, to the best of my knowledge and belief, title .
	y:

DECLARATION FOR PATENT APPLICATION

As a below-named inventor, I hereby declare that this declaration is for the national phase f the PCT.

My residence, post office address and citizenship are as stated below, next to my name. I believe I am an original, first and joint inventor of the subject matter which is claimed and for which a patent is sought on the invention entitled: NITRIDE SEMICONDUCTOR DEVICE

International Application No. PCT/JP98/03336 filed on Feb. 4, 1998. I hereby state that I have reviewed and understand the contents of the above-identified specification, including the claims, as amended by any amendment referred to above. I acknowledge the duty to disclose information which is material to the examination of this application in accordance with Title 37, Code of Federal Regulations, Section 1.56(a).

I hereby claim foreign priority benefits under Title 35, United States Code, § 119 of any foreign application(s) for patent or inventor's certificate or any PCT International application(s) designating at least one country other than the United States listed below and have also identified below any foreign application for patent or inventor's certificate or any PCT International application(s) designating at least one country other than the United States filed by me on the same subject matter having a filing date before that of the application on which priority is claimed:

Prior Foreign Application(s)	rior Foreign Application(s)		Priority Claim	
		05 (07 (10 07	Yes	No
P 9-199471	Japan	25/07/1997	Х	
Number	Country	Day/Month/Year Filed		
P 9-235524	Japan	01/09/1997 .	Х	
Number P 9-286304	Country	Day/Month/Year Filed		
₽ 9-286304	Japan	20/10/1997	Х	
Number	Country	Day/Month/Year Filed		<u> </u>
P 9-304328	Japan	06/11/1997	Х	
Number	Country	Day/Month/Year Filed		
P 9-317421	Japan ·	18/11/1997	Х	
Number	Country	Day/Month/Year Filed		
P 9-348972	Japan	18/12/1997	х	
Number	Country	Day/Month/Year Filed		
P 9-348973	. Japan	18/12/1997	х	
Number	Country	Day/Month/Year Filed		
P 10-176623	Japan	08/06/1998	Х	
Number	Country	Day/Month/Year Filed		
P 10-176634	Japan	08/06/1998	х	
Number	Country	Day/Month/Year Filed		
P 10-199829	Japan	29/06/1998	Х	
Number	Country	Day/Month/Year Filed		

I hereby claim the benefit under Title 35, United States Code, § 120 of any United States application(s) listed below and, insofar as the subject matter of each of the claims of this application is not disclosed in the prior United States application in the manner provided by the first paragraph of Title 35, United States Code, § 112, I acknowledge the duty to disclose material information as defined in Title 37, Code of Federal Regulations, § 1.56(a) which occurred between the filing date of the prior application and the national or PCT International filing date of this application:

Application Serial No.	Filing Date	Status: Patented, Pending, Abandoned

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

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